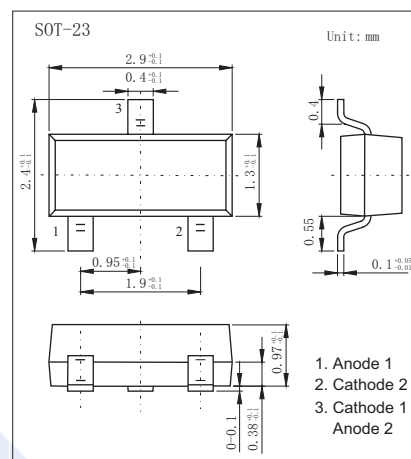
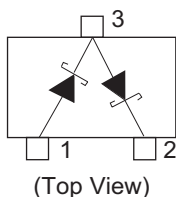


Schottky Diodes

HSM88AS

■ Features

- Proof against high voltage.
- Suitable for high density surface mounting and high speed assembly.

■ Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Reverse Voltage	V_R	10	V
Average rectified current (Note 1)	I_O	15	mA
Junction Temperature	T_j	125	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 to 125	

■ Electrical Characteristics ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Forward voltage	V_{F1}	$I_F = 1\text{ mA}$	0.35		0.42	V
	V_{F2}	$I_F = 10\text{ mA}$	0.50		0.58	
Reverse current	I_{R1}	$V_R = 2\text{ V}$			0.2	μA
	I_{R2}	$V_R = 10\text{ V}$			10	
Capacitance	C	$V_R = 0\text{ V}, f = 1\text{ MHz}$			0.85	pF
Capacitance deviation	ΔC	$V_R = 0\text{ V}, f = 1\text{ MHz}$			0.10	
Forward voltage deviation	ΔV_F	$I_F = 10\text{ mA}$			10	mV
ESD-Capability (Note 2)		C = 200 pF, R = 0 Ω , Both forward and reverse direction 1 pulse.	30			V

Note 1. Per one device

2. Failure criterion ; $I_R \geq 0.4\text{ }\mu\text{A}$ at $V_R = 2\text{ V}$

■ Marking

Marking	C1
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Schottky Diodes

HSM88AS

■ Typical Characteristics

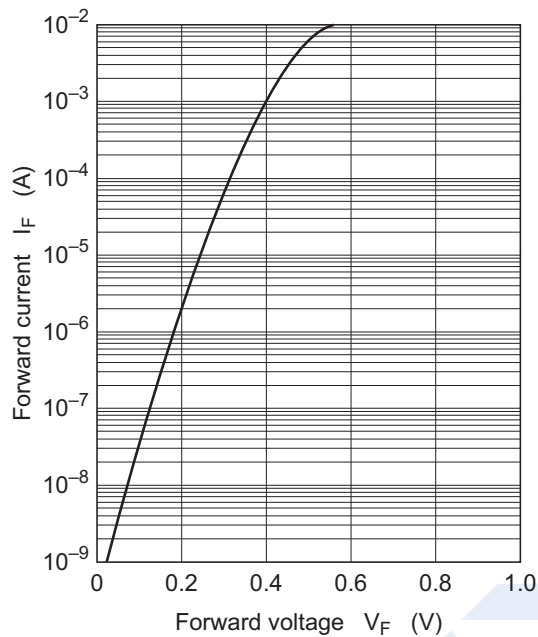


Fig.1 Forward current vs. Forward voltage

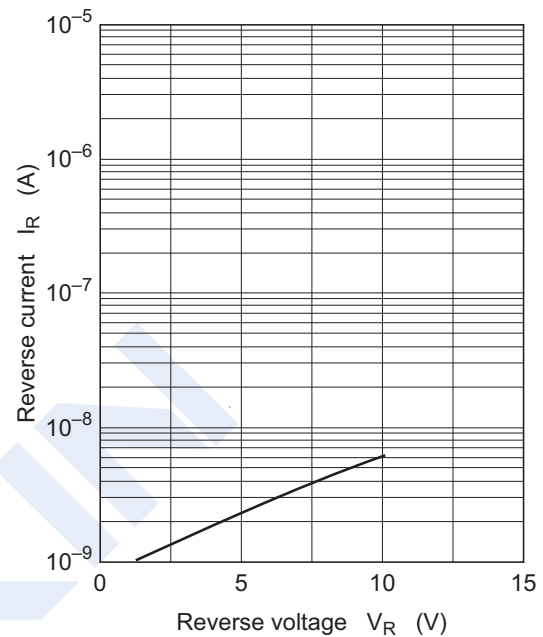


Fig.2 Reverse current vs. Reverse voltage

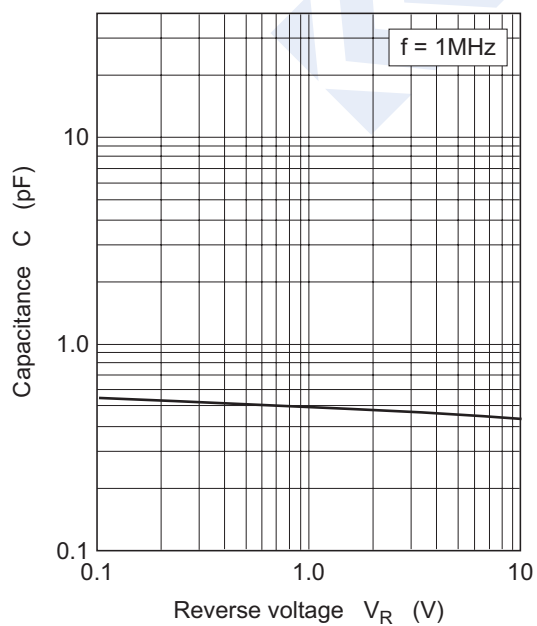


Fig.3 Capacitance vs. Reverse voltage